# Covert Gates: Protecting Integrated Circuits with Undetectable Camouflaging

Bicky Shakya, Haoting Shen, Mark Tehranipoor and Domenic Forte

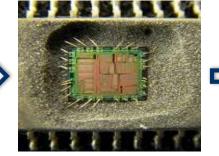


## **Rise of Automated Reverse Engineering**





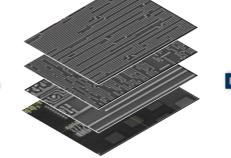
Chip



#### De-packaging

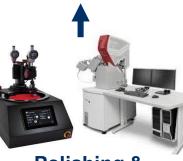


Chemicals & Abrasion

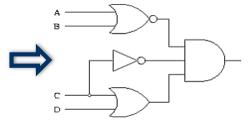


Source: Quijada, Raul, et al., *Journal of Hardware and Systems Security, (2018)* 

#### **De-layering & Imaging**



Polishing & Delayering



Source: scienceasart.org

#### **Layout Generation**

**Netlist Extraction** 



**Analysis** 

Source: micronetsol.net, texplained.com

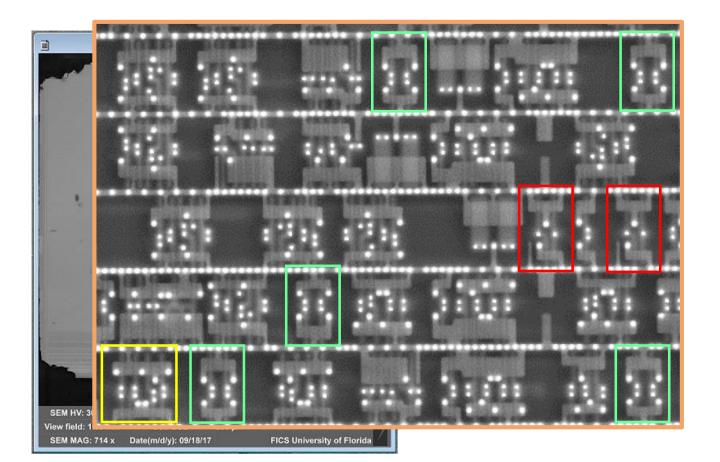
- Evaluate its performance and functionality
- □ See if it infringes your patents
- See how competitor product matches up

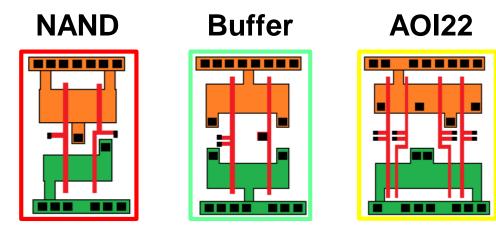
- □ Integrate the IP into an attacker's design
- Clone the design
- Find and exploit vulnerabilities in the design

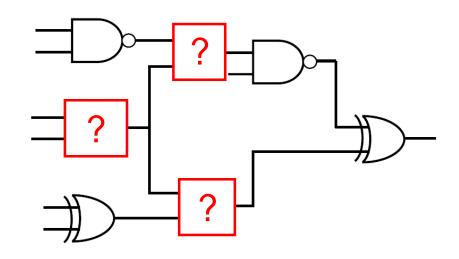
## What is IC Camouflaging?



Main Goal: Protect IP from Reverse Engineering Stakeholders: Commercial Semiconductor Design Houses and Fabless Vendors, IP Providers (even Foundries), and Government (esp. Defense)





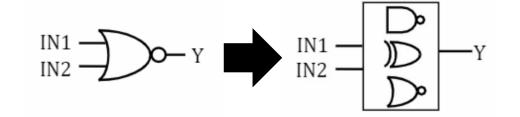


**Camouflaged Netlist** 

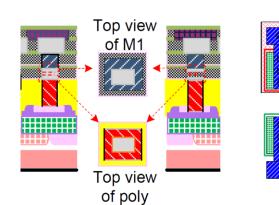
## **Existing Camouflaging Techniques**

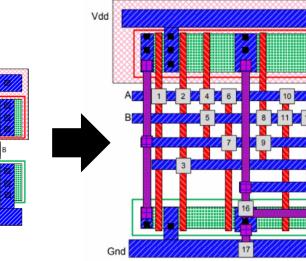


Camouflaging (Camo) Gate: hide the real gate's function



### Camouflaging Gate Design Examples





**Drawbacks** 

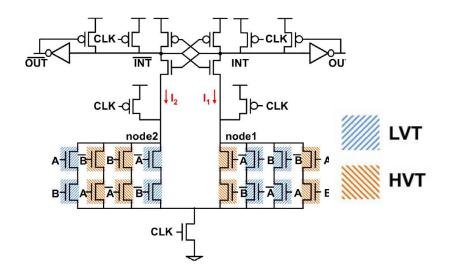
- 4-5x Larger Power and Area

**Dummy Contact** 

[Rajendran et al, CCS 2013]

### **Threshold-Voltage Modification**

[Erbagci et al., HOST 2016]



- Different Logic Style
- > 2x Area, 1.5x Delay, and 10% Power

## **Scope and Adversarial Model**



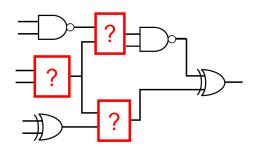


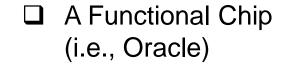
### Assumption #1 (Defense): Foundry is trusted

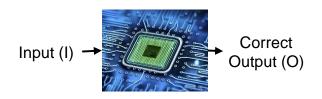
- Plays an active role in protecting the IP
- May even provide library of camo cell technologies
- Does not leak GDSII, mask sets, etc.

### Assumption #2 (Attack): The following are available to the attacker

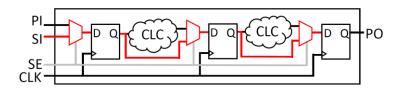
A Camouflaged Netlist (obtained by RE)





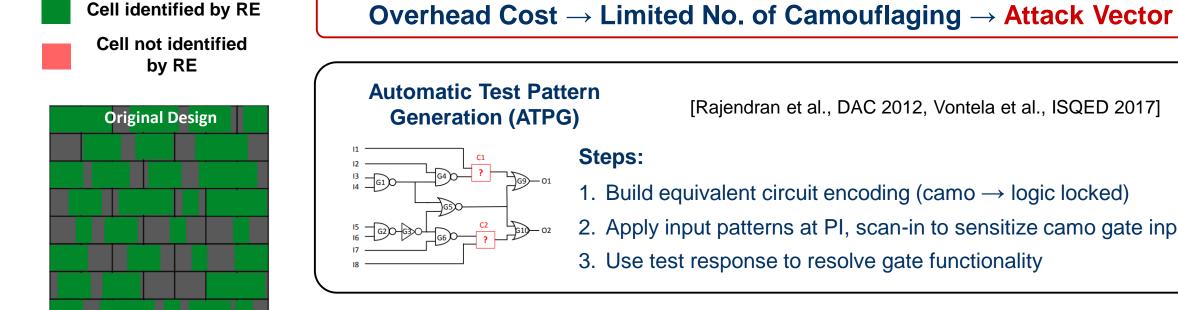


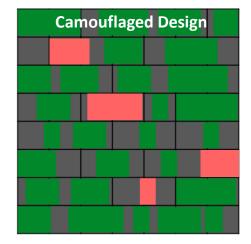
□ Scan Chain Access



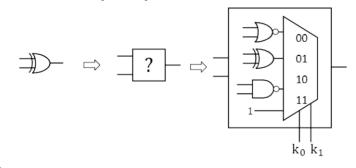
## **Attacks on Prior IC Camouflaging Approaches**







#### Satisfiability-based (SAT) Attack



[Massad et al., NDSS 2015, Subramanyan et al., HOST 2015]

#### Steps:

- 1. Build equivalent circuit encoding
- 2. Observe the satisfiability using oracle
- 3. Rule out incorrect assignments

#### [Rajendran et al., DAC 2012, Vontela et al., ISQED 2017]

- 1. Build equivalent circuit encoding (camo  $\rightarrow$  logic locked)
- 2. Apply input patterns at PI, scan-in to sensitize camo gate inputs
- 3. Use test response to resolve gate functionality

## **Proposed Approach: 'Covert' Camo Gate**

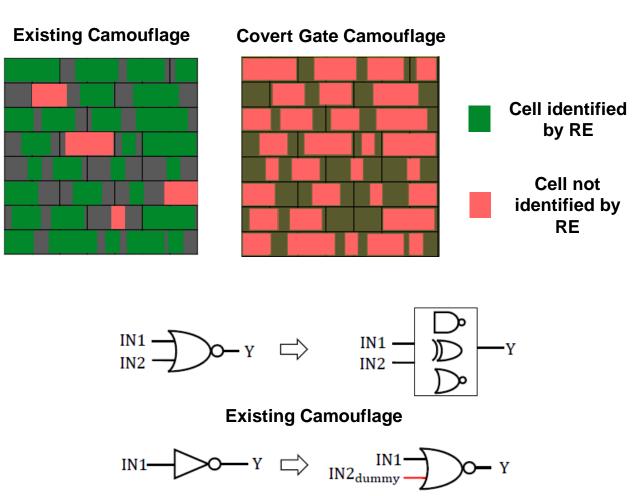


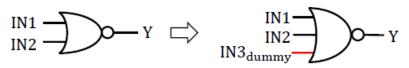
### Requirements

- Every camouflaged gate should look like any other gate in a standard cell library
  - All gates become suspect!
  - Expected to drastically increase invasive and non-invasive attack complexity

### **Covert Gate**

- Expand n input gates into n + i input gates (where i is # of dummy inputs)
  - + Much lower leakage/area/delay expected with dummy inputs
  - + No change in logic style





**Covert Gate Camouflage** 

### **Regular MOSFET modification**

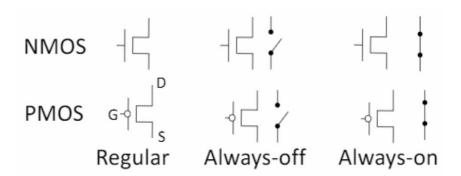
Switchable transistors  $\rightarrow$  [Always-On] or [Always-Off] Modification is <u>INVISIBLE</u> by SEM

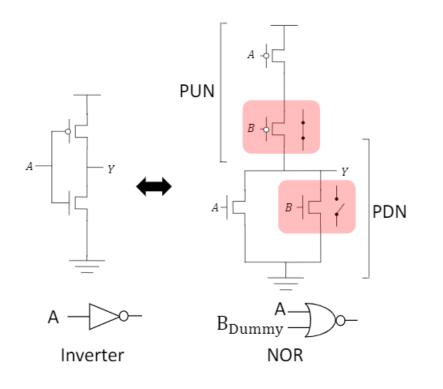
### **Complementary structure is necessary:**

- 1. Enable functional gates
- 2. Keep the static current leakage low

### Implemented modification: <u>Dummy Inputs</u>

- Always-On in the
- pull-up
- Always-Off in the pull-down
- Always-Off in the pull-up
  - Always-On in the pull-down

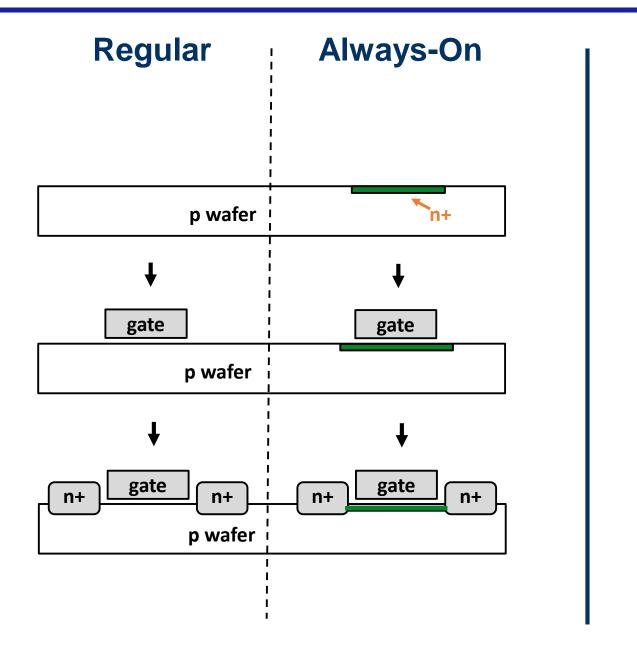


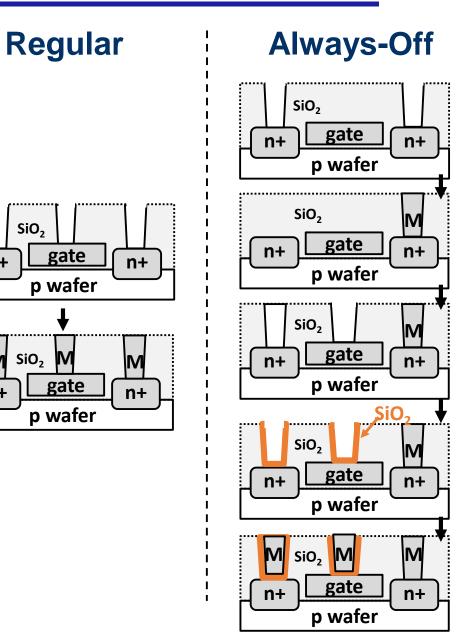




## **Device Structure and Fabrication of Covert Gates**







SiO<sub>2</sub>

SiO<sub>2</sub> M

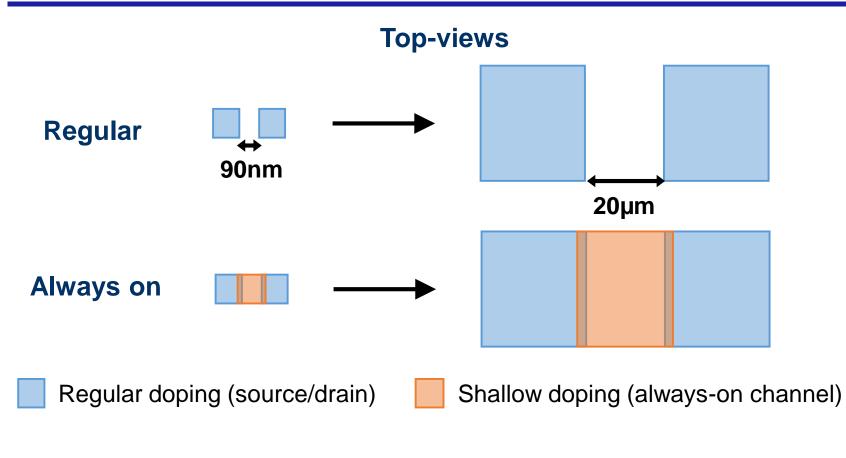
n+

M

n+

## 'Always on' Prototype Structure



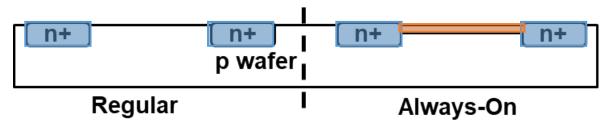




**TESCAN LYRA-3** 

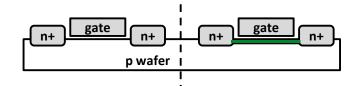
Imaging Settings						
SE	BSE					
15 keV	15 keV					
10 keV	10 keV					
5 keV	5 keV					
800 eV	N/A					

#### **Cross-sections**

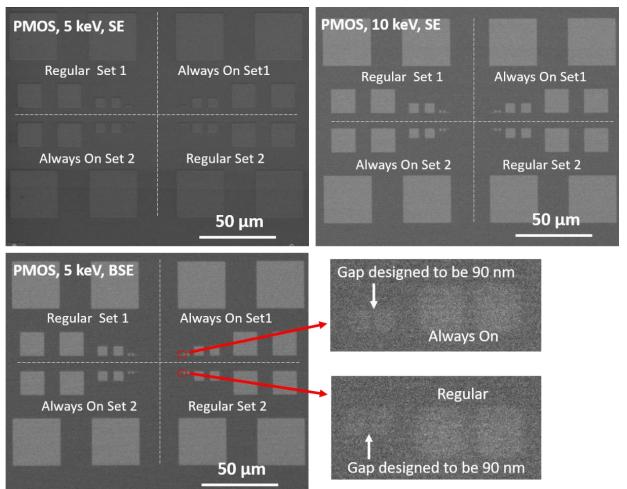


## Imaging Results – Regular vs. Always-On

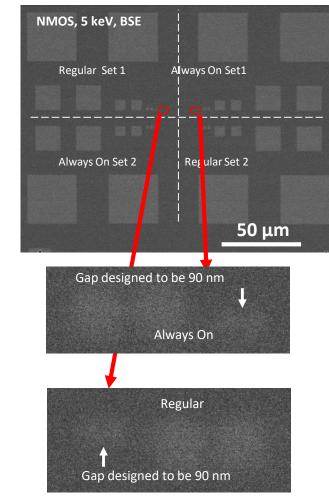




#### **PMOS**

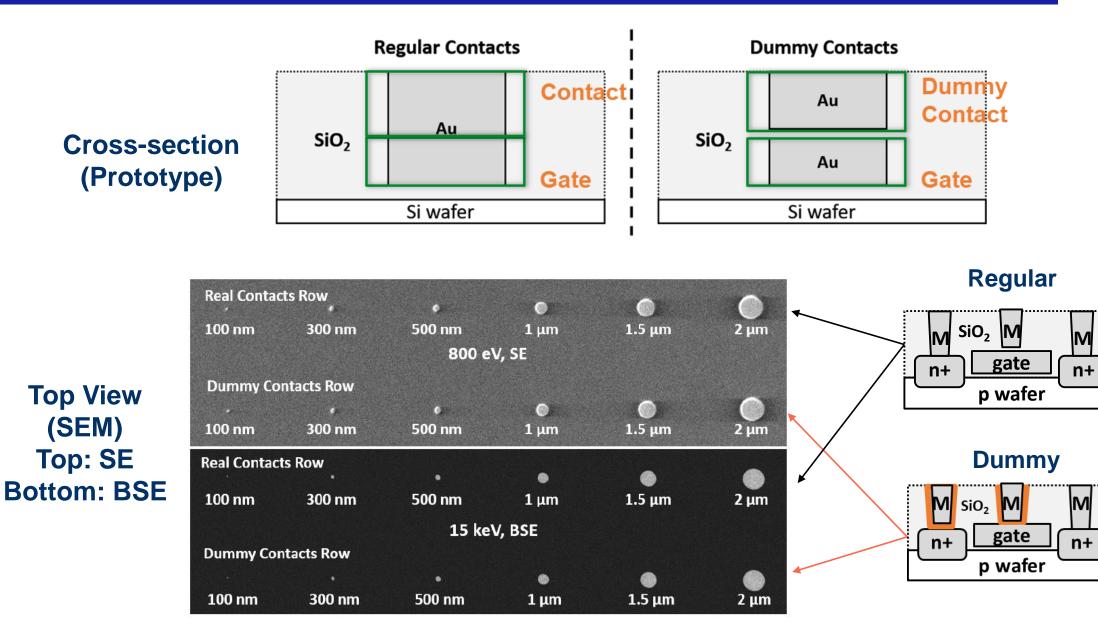


#### NMOS



## Imaging Results – Regular vs. Always-Off



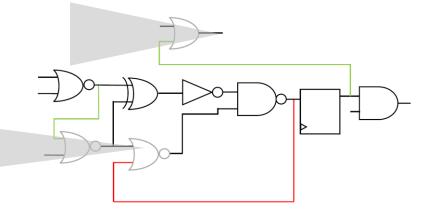


## **Experimental Setup**



Higher Attack Complexity	camouflaged	some types of gates are ouflaged NAND/NOR/XOR/AND/OR)			ew pins of n be dumr pin of all I	Lower Attack Complexity	
<ul> <li>Less</li> <li>knowledgeable</li> <li>attacker</li> </ul>	5	4	3	gates)	2	1	<ul> <li>More knowledgeable attacker</li> </ul>
No information on which gates are camouflaged		gates are c	Only one (or few) ty gates are camoufla (e.g., only NAND/N		laged (and speci		

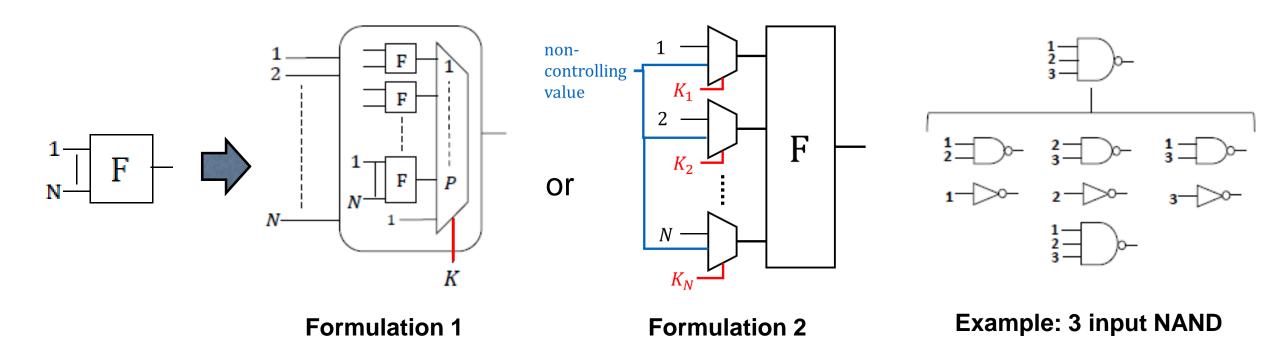
- SAT Attack: Scenario #3, timeout set at 12 hours
- **Test-based Attack:** Scenario #2
- Covert Gate Insertion: Random, but combination feedbacks are not allowed



Fan-in cone modification, enabled by dummy inputs

## **SAT Attack Formulation on Covert Gates**





- Correct key chooses correct pins **based on oracle response**
- Complexity increase with
  - No. of pins on suspect gates
  - No. of candidate gates  $\rightarrow$  all gates
  - Increased conjunctive normal form (CNF) formula size  $\rightarrow$  Larger search space

## **SAT Attack Results**



	Gate /	Existi	ng Camo	Proposed Camo (Covert)		
Benchmark	Node Count	<i>K</i>	K  Attack Time (s)		Attack Time (hrs) Form 1 [Form 2]	
C1908	880	34	0.55	811	3.52 [5.91]	
C2670	1193	26	0.65	1514	Timeout [Timeout]	
C3540	1669	28	0.68	2088	Timeout [Timeout]	
C5315	2307	46	3.58	3379	Timeout [4.27]	
C7552	3512	106	4.07	4454	Timeout [Timeout]	
arbiter	11,839	1182	3815.00	23,678	Timeout [Timeout]	
voter	13,758	1078	Timeout	21,560	Timeout [Timeout]	

### **SAT Attack Complexity**

□ Increased key size

 $\Box$  SAT attack timeout (12 hrs) $\rightarrow$  More iterations / More time per iteration

#### Generate a test to check whether pin is dummy or functional.

- Control: Assert controlling value on suspect pin (using s-a-0, s-a-1)
- **Observe:** Non-controlling values on other pins and nets to propagate to observe point

#### **Possible Scenarios**

- Detectable: it can be determined with certainty whether a pin on the gate is dummy or not
- Undetectable: the dummy pin has no effect on the output 'ATPG
- **Untestable:** a test pattern cannot be generated to sensitize and propagate a controlling value on a potentially dummy pin
- Not Detected: test pattern to detect the pin could not be generated with tool effort level

Benchmark	Cata	Gate	Gate Detectable		Undetectable		ATPG Untestable		Not Detected	
Denchinark	Gate	Count	#	%	#	%	#	%	#	%
b18 Primitive Count = 84,632 #Scan DFF = 3,020 I/O = 40/24	NOR2X	2390	10	0.42	5	0.21	2873	99.29	2	0.08
	NOR3X	270	12	4.44	0	0.00	237	87.78	21	7.78
	NOR4X	195	17	8.72	0	0.00	114	58.46	64	32.82
	NAND2X	4194	7	0.17	30	0.72	4154	99.05	3	0.07
	NAND3X	2135	8	0.37	19	0.89	1849	86.60	259	12.13
	NAND4X	909	38	4.18	0	0.00	753	82.84	118	12.98



### Attack succeeds Attack fails

> 91%

Legend

## **Circuit Overhead and Corruptibility Results**



Benchmark	Area (µm²)		[	Delay (ns)			ower (µW)	Verification		
	Covert	Original	%	Covert	Original	%	Covert	Original	%	Failure (%)
AES	114,098	113,384	0.63	18.19	15.99	13.76	2,689	2,678	0.38	80.42
b12	9,725	9,646	0.81	2.98	2.88	3.46	154	154	0.35	54.33
b15	53,432	53,134	0.56	26.32	26.32	0.00	654	657	-0.38	94.66
b17	171,193	170,264	0.54	32.47	31.14	4.27	2,015	2,011	0.22	91.37
s35932	111,402	111,088	0.28	14.13	10.84	30.35	2,290	2,328	-1.67	90.87
s38417	107,803	107,349	0.42	20.84	16.69	24.87	1.949	1,949	-0.03	54.85
s38584	87,647	87,229	0.48	15.38	13.11	17.32	1,572	1,570	0.08	70.29

- *Minimal area overhead.* Proposed camo cells are no larger than standard logic gates (AND2X1, NAND2X1 etc.)
- Power overhead minimal
- Delay penalty due to random insertion. Can avoid critical paths for further optimization
- High Corruptability. Even when covert gates are inserted randomly, there are large number of percentage mismatches with original design



### We are grateful for the sponsors of this project:



### Thank you to the partners and sponsors of UF/FICS SCAN Lab:



### Covert gates

- Indistinguishable from regular gates (i.e., imaging resistant)
- Very strong deterrents against oracle-based and probing-based reverse engineering
- Inexpensive to fabricate
- Lower overhead than existing camo gates

### **Future Work**

- Formal proofs of security against oracle attacks
- Investigate oracle-less attacks (e.g., structural) against covert gate circuits
- Explore covert gate insertion strategies w/ security and overhead in mind
- Fabricate and characterize real covert gate devices
- Image using He-Ne ion microscopes





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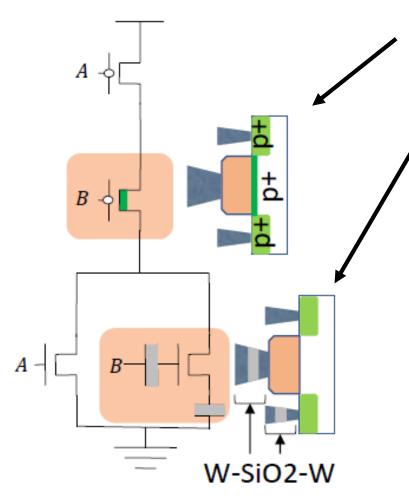
## **Covert Gate Distribution for SAT Evaluation**



Bonohmark Total %		2 inp	ut	3 inp	out	4 input	
Benchmark Cove	Covert	AND/NAND	OR/NOR	AND/NAND	OR/NOR	AND/NAND	OR/NOR
C1908	45%	43%	0%	1%	0%	0%	0%
C2670	56%	38%	5%	9%	0%	1%	2%
C3540	56%	41%	4%	6%	5%	1%	0%
C5315	60%	34%	5%	16%	2%	1%	3%
C7552	58%	44%	6%	4%	1%	2%	1%
arbiter	100%	100%	0%	0%	0%	0%	0%
voter	100%	100%	0%	0%	0%	0%	0%

## **Covert Gate Circuit Model**



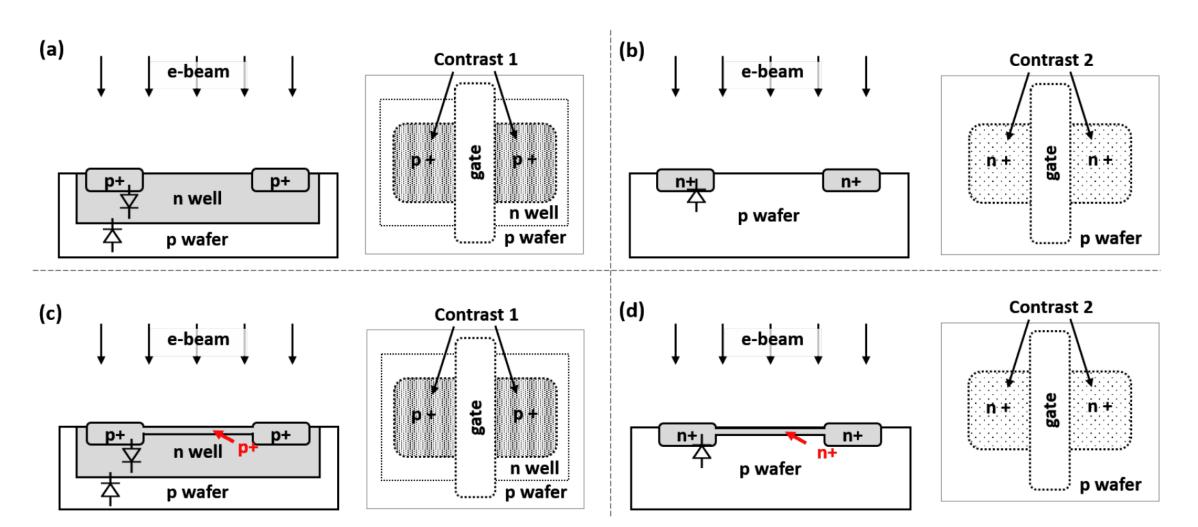


- Always-on FET emulated by depletion mode device where channel is 'pre-formed'
- Always-off FET emulated by SiO2 insulator in gate and source contacts

### **Overhead Cost (SPICE Simulations)**

Dummy-based Camouflaging Gates				Proposed Covert Gat (Compared to INVX)			
Area	Delay	Power		Area	Delay	Dyn Power	Static Power
4 X	1.6 X	5.5 X	NAND2X1	0.86X	1.34 X	0.72 X	0.22X
4 X	1.1 X	5.1 X	NOR2X1	1.00X	1.82 X	0.69 X	0.27X

## **Effective Conduction Volumes (Proposed)**



/IF

UNIVERSITY of

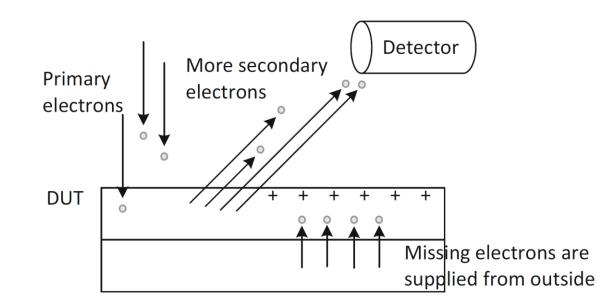
Research

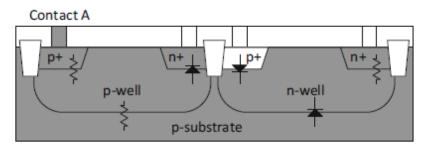
## **Reversing Stealthy Dopant-level Trojans**

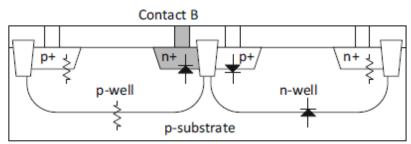


Sugawara et al, CHES 2014

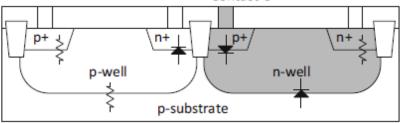
- Passive Voltage Contrast (PVC) is a measurement principle used by SEM/FIB to measure surface voltage of a sample
- Dopant configurations used by dopant-level Trojans can be distinguished with PVC even when a chip is measured at power-off state!

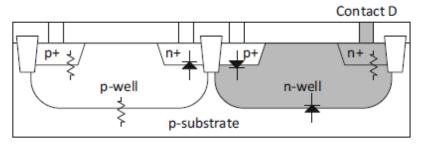






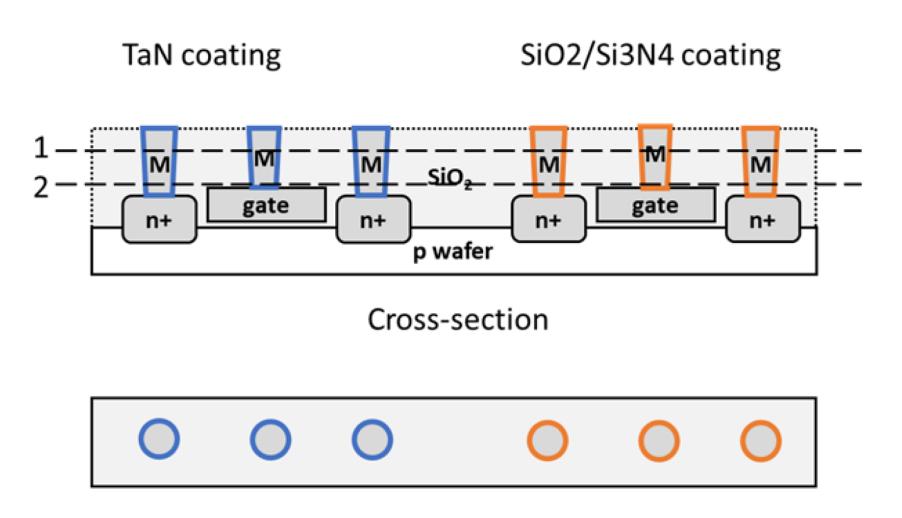






**Etching** 





**Top View** 

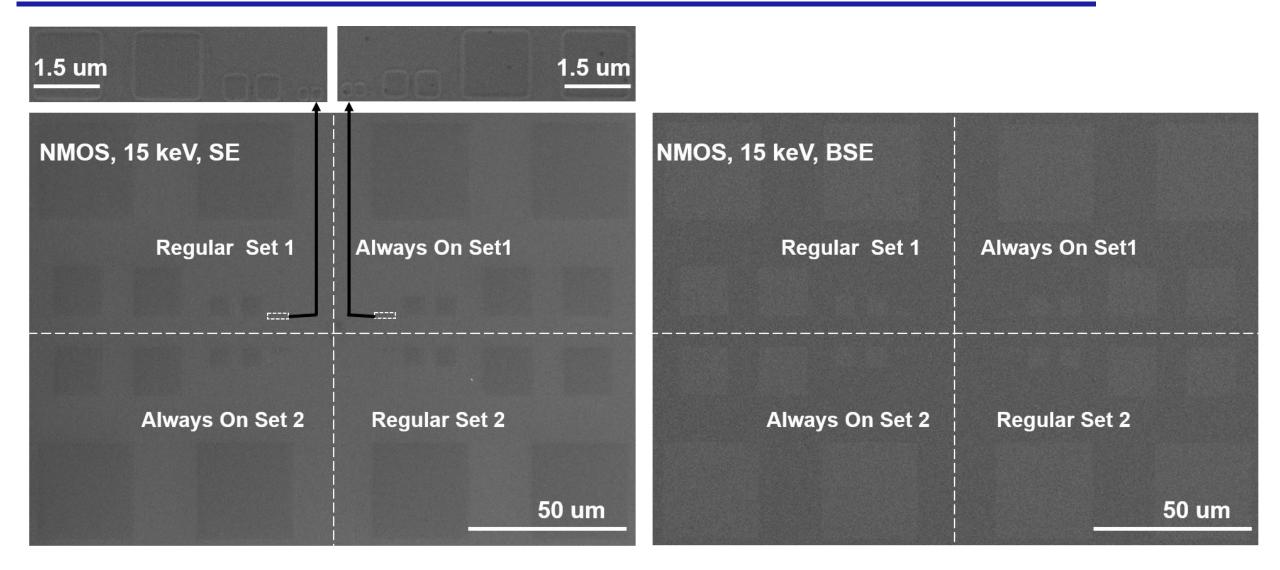
## **Comparison to Other Camouflaging Techniques**



Feature		Covert			
reature	Dummy	Threshold	Doning	Transformable	Gates
	Contact	Voltage	Doping	Interconnects	
SAT resistant at low overhead	×	×	×	×	1
Test attack resistant	×	×	×	×	✓
Low overhead	×	×	×	×	✓
Configurable after fabrication	×	1	×	×	×
Imaging resistant	1	✓	✓	?	✓
Undetectable during netlist extraction	×	×	×	×	✓

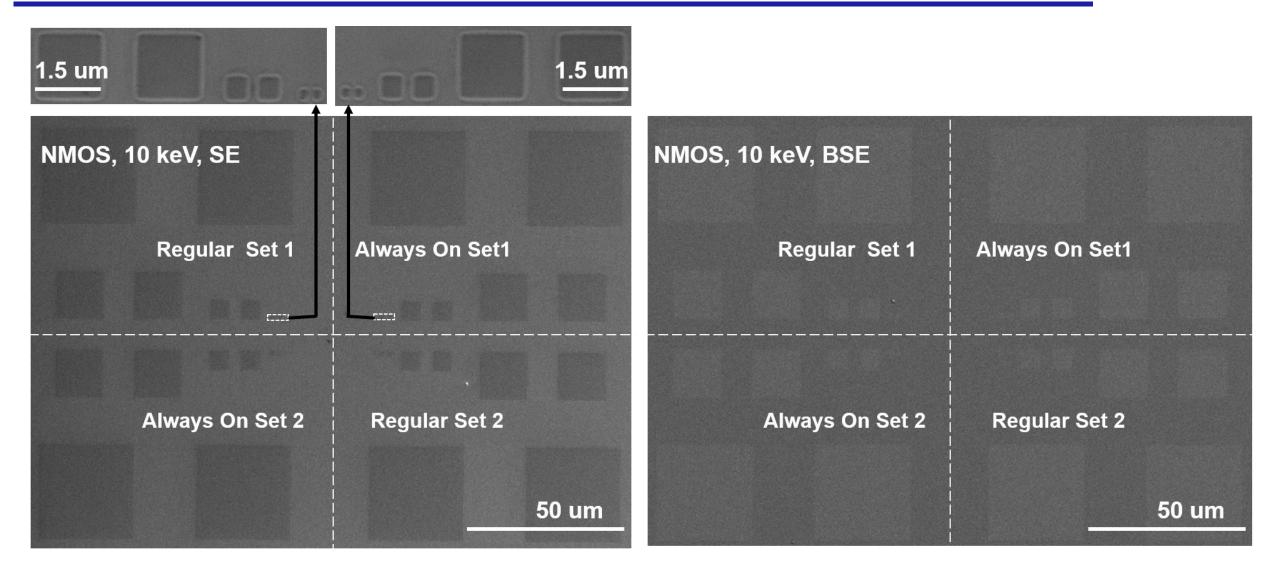
## SEM Images: NMOS, 15 keV, SE and BSE





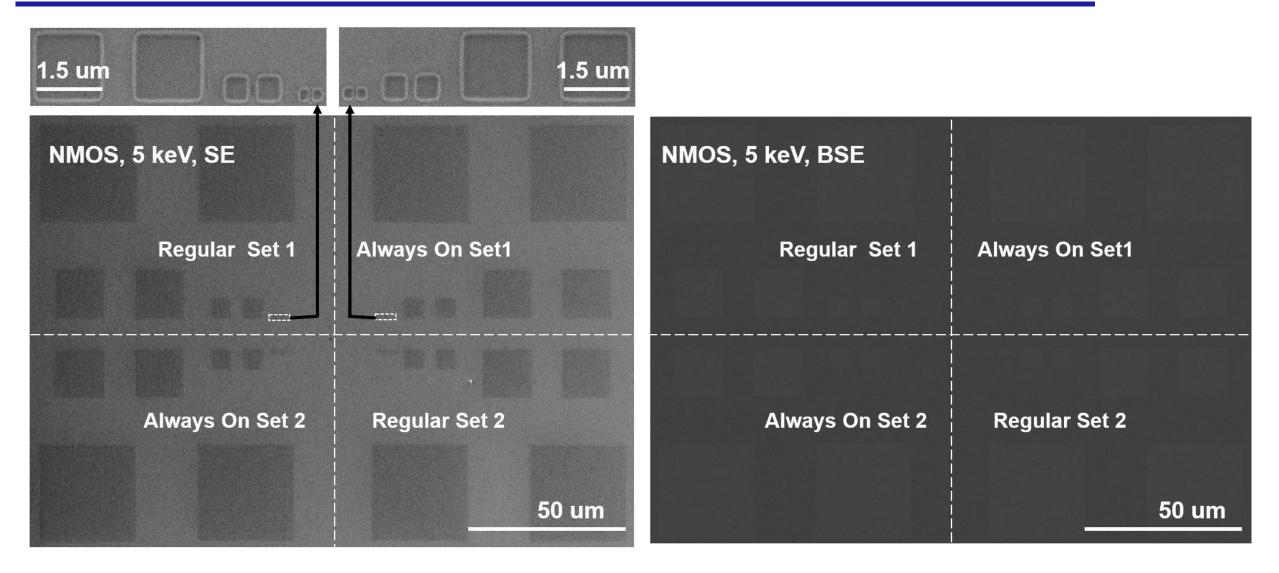
## SEM Images: NMOS, 10 keV, SE and BSE





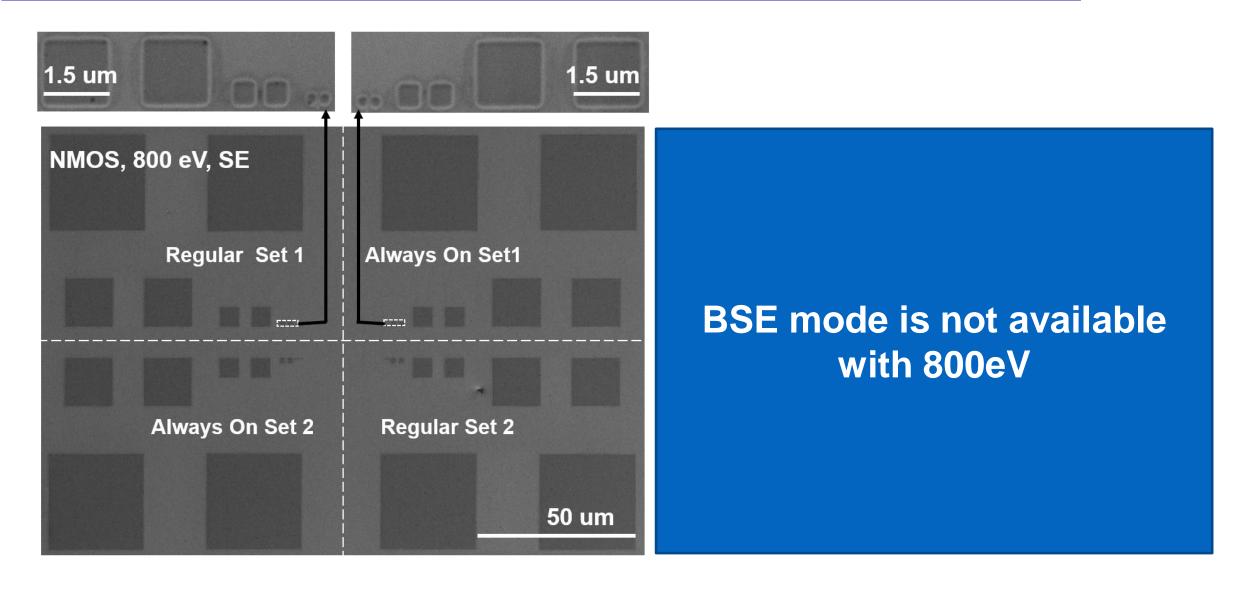
## SEM Images: NMOS, 5 keV, SE and BSE





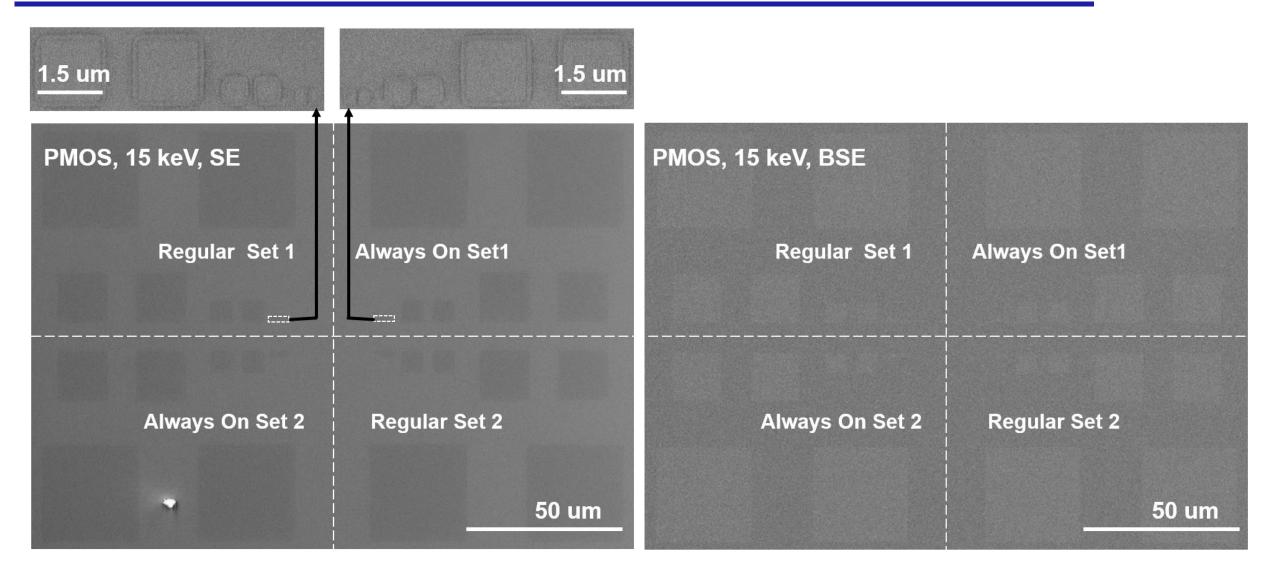
## SEM Images: NMOS, 800 eV, SE and BSE





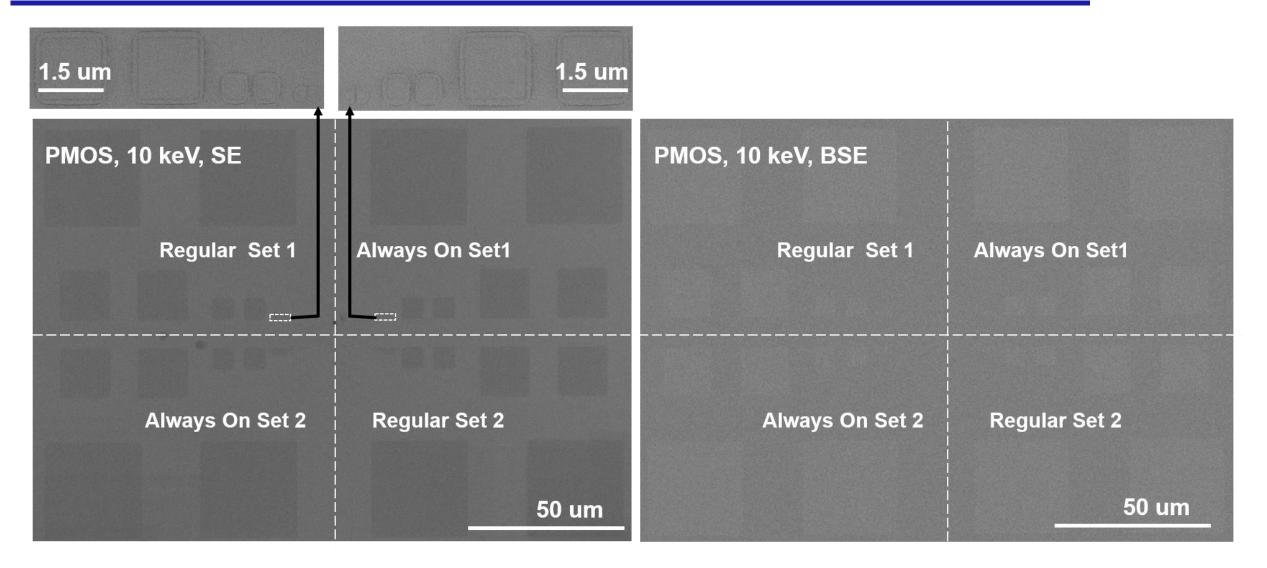
## SEM Images: PMOS, 15 keV, SE and BSE





## SEM Images: PMOS, 10 keV, SE and BSE





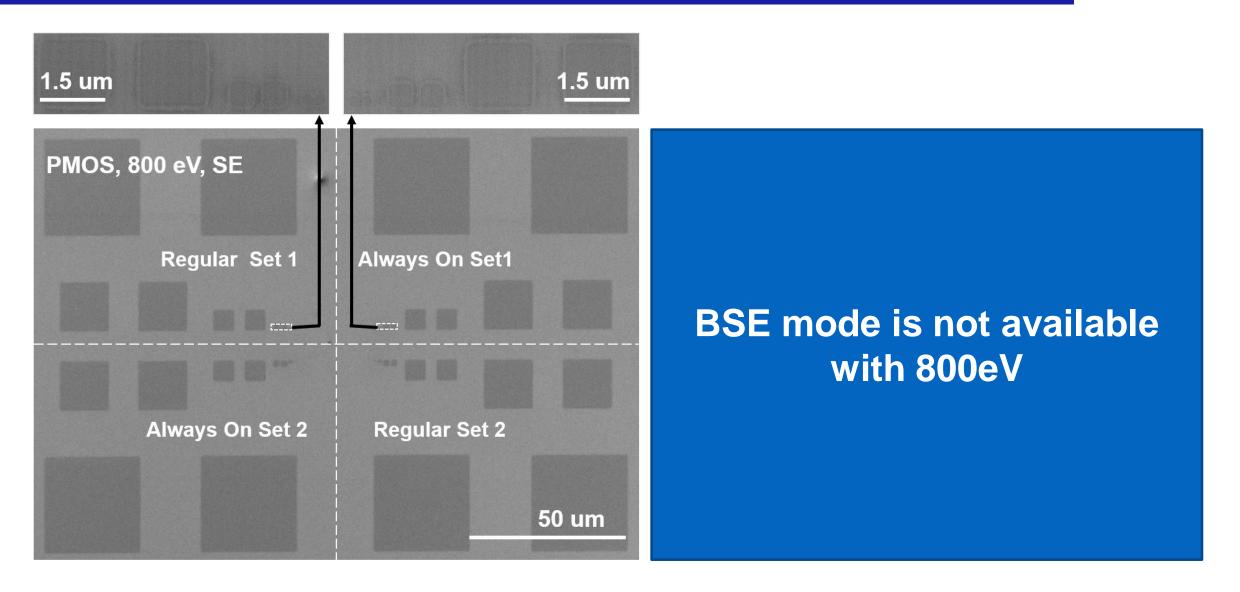
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1.5 um	1.5 un		
PMOS, 5 keV, SE		PMOS, 5 keV, BSE	
Regular Set 1	Always On Set1	Regular Set 1	Always On Set1
Always On Set 2	Regular Set 2	Always On Set 2	Regular Set 2
	50 um		<u> </u>

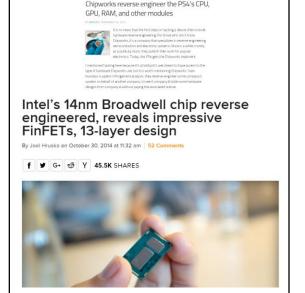
## SEM Images: PMOS, 800 eV, SE and BSE





## **IP Issues in the Public Domain**





**Reverse Engineering** 



#### Engineer Says He Stole Secrets Of Chip Makers





an Argentine engineer says he tobe a wide range of rechnical secrets from the leading computer chip makers in the United States and provided the information to China. Colus and Iran. The technical information, he said, included computer chip designs and step begins the priority of the said secret form the said secret secr

Ex-Intel Worker In Guilty Plea

colleress Gaule, who originally alcoded not milty to charms of mail fo

Blockbuster Qualcomm lawsuit claims Apple stole modem tech and gave it to Intel







#### From the SEMI President and CEO

Innovation is at Risk: Losses of up to \$4 Billion Annually due *Very* Stage. to IP Infringement

Protection of intellectual property (IP) rights is an important area of concern for the semiconductor manufacturing industry. In a competitive global business environment, IP protection is essential to the survival of equipment and materials suppliers, enabling them to invest the significant R&D funds needed to sustain technological advancement of the semiconductor industry.

In recent years, suppliers have been increasingly funding a larger portion of the escalating R&D costs needed for the continued success of the semiconductor device industry. These challenging conditions pose a serious

The **Register** Riding the hand that foods 17

#### forr Security

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IP

- ma Boffins deduce chip's crypto just by looking at it
- In re Smartcard hacking enters script-kiddie phase

By Dan Goodin 4 Aug 2011 at 04:35 19 📮 SHARE ▼

Cha Black Hat Hackers have released tools that unlock the software stored on heavily fortified chips so researchers can independently assess their security and spot weaknesses.

At the heart of the the release, which was announced Wednesday at the Black Hat Security conference in Las Vegas, is Degate, software developed by Martin Schobert for hardware experts to analyze small silicon structures. It has recently been refined so it can be used by tinued IP violations of various generation equipment and aw technology curve.

orts in protection and enforcement of udy on the extent and impact of IP on the survey findings, is now

### zed semiconductor supply ds to the possibility of **IP e and compromise** *at*

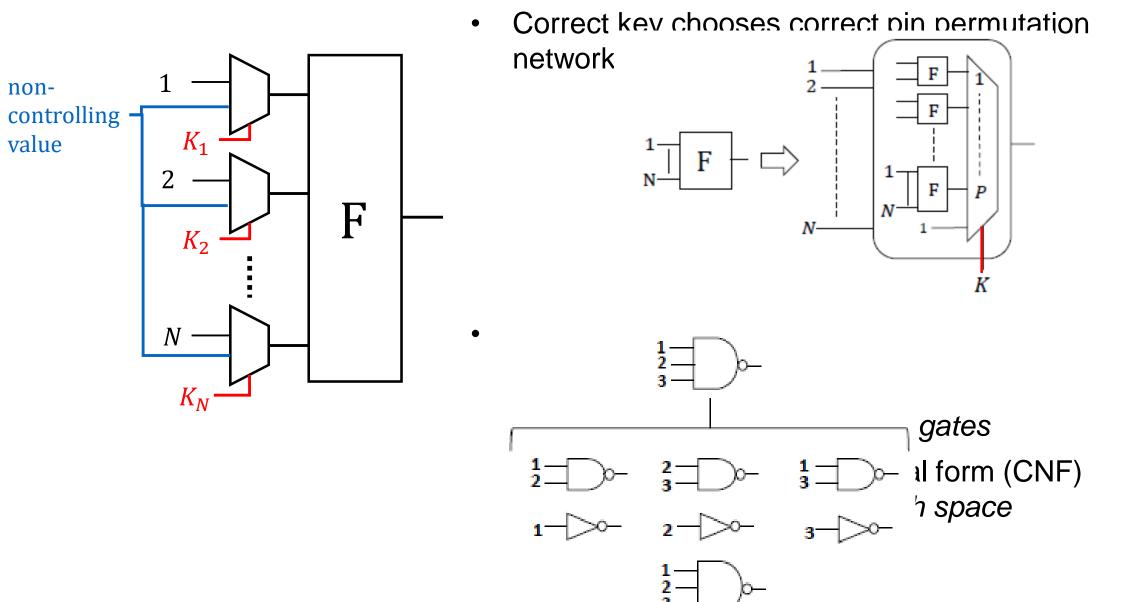
equences range from lost ue to design tampering.

backbone of every chip ind needs *active on mechanisms* at various abstraction in the supply



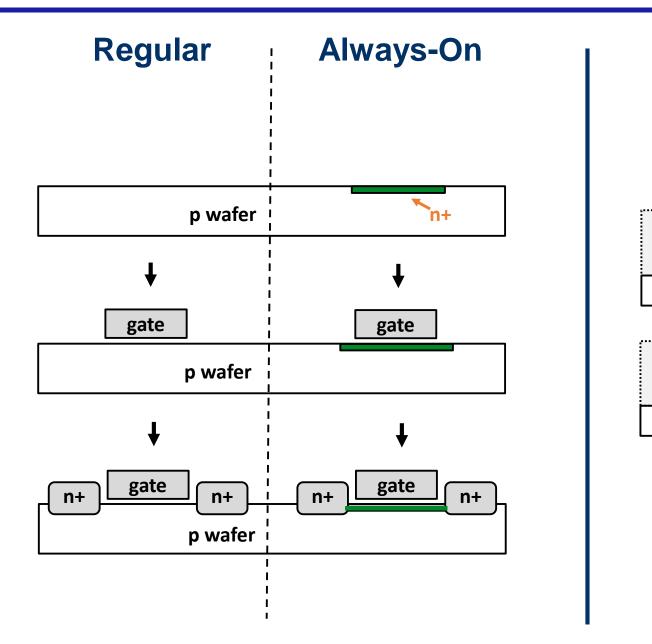
## **SAT Attack Formulation on Covert Gates**

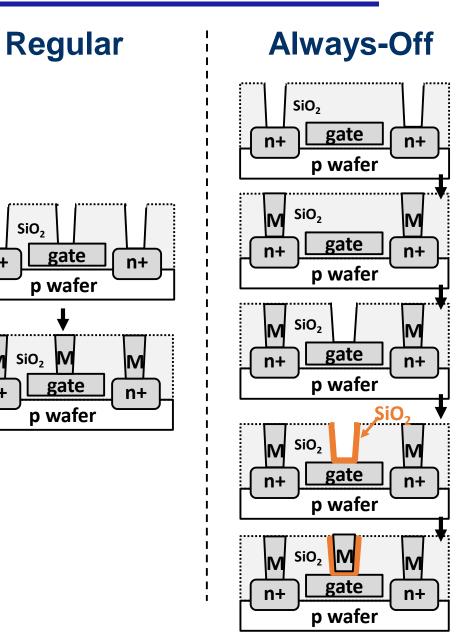




## **Device Structure and Fabrication of Covert Gates**







SiO<sub>2</sub>

n+

M

n+